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AC-LGAD Sensor Status and Plan

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January 2023 ePIC Collaboration Meeting

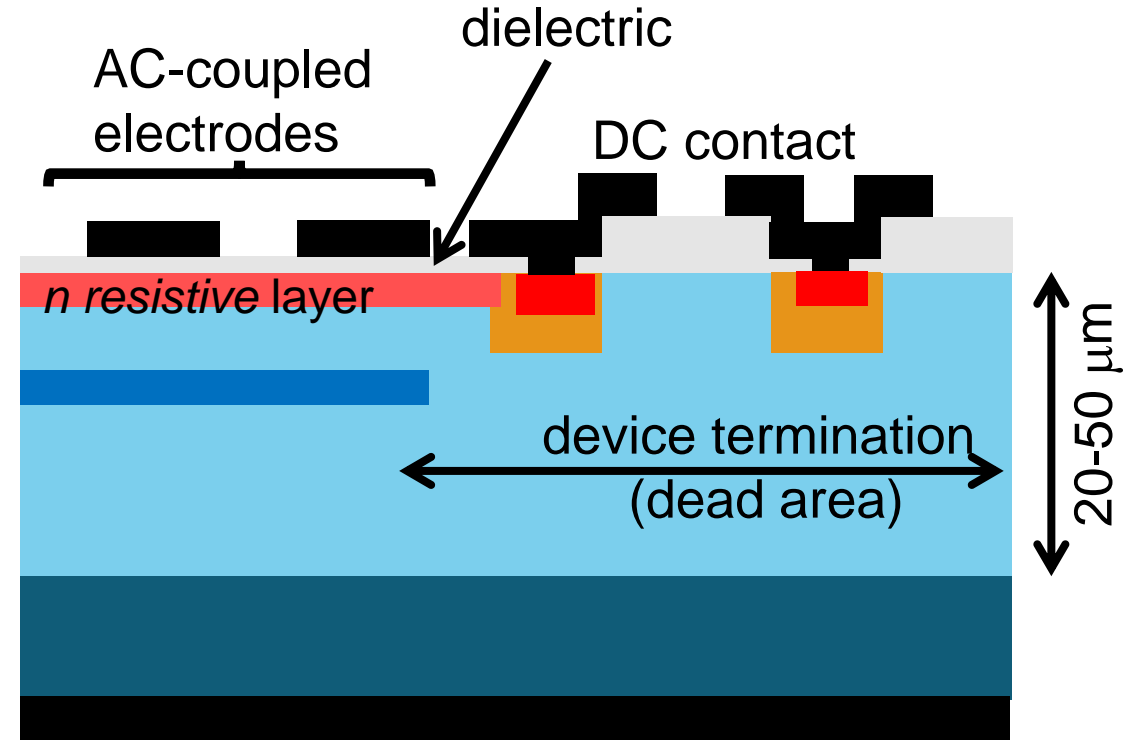
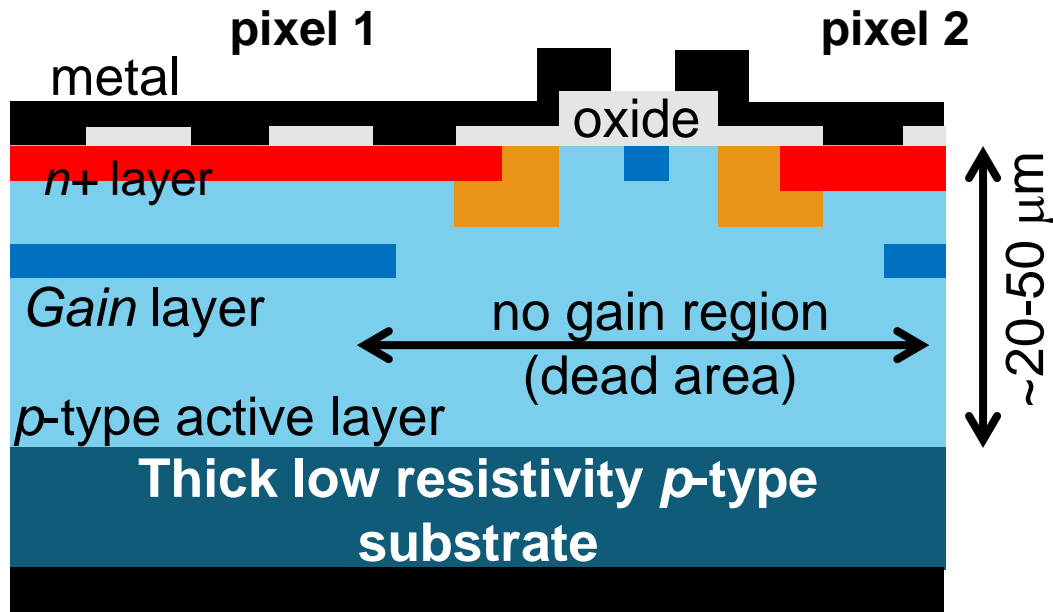
1/11/2023



LGAD vs AC-LGAD

Low-Gain Avalanche Diodes show good timing resolution (30ps) but poor spatial resolution, due to large dead area at the pixel border.

4D detector not possible and other devices are needed.



Metal (back contact)

Capacitively-Coupled Low-Gain Avalanche Diodes have large uniform area for 100% fill factor (no dead areas), and potentially same timing resolution. Excellent spatial resolution when signal sharing is used to interpolate hit position.

Process modification needed to pass from LGAD to AC-LGAD but still feasible in standard Clean Room.

BNL Clean Room for silicon sensors

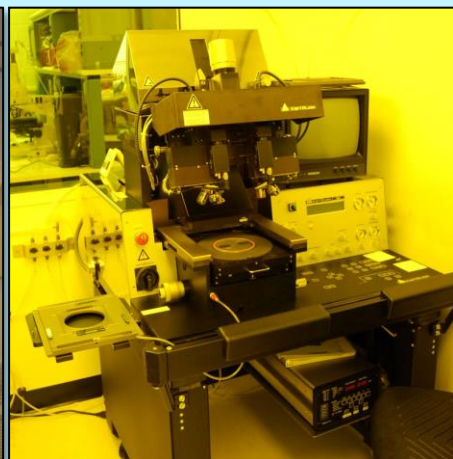
LGAD and AC-LGAD can be fabricated at BNL, using standard tools.

Ion Implantation is outsourced: paramount importance process step that dictates gain.

All silicon process done in BNL Instrumentation Division Class-100 Clean Room



Furnaces for high-quality SiO_2 growth and annealing



Double-sided mask aligner



Wet bench (HF, RCA I & II, piranha, ...)



Sputtering (Al, Al1%Si, Ti)



RTA for sintering

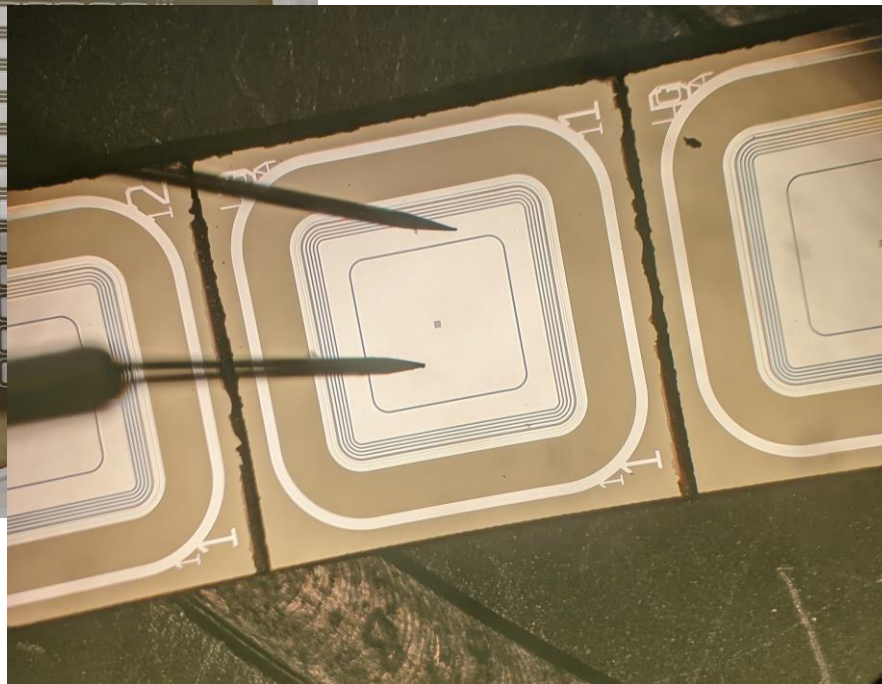
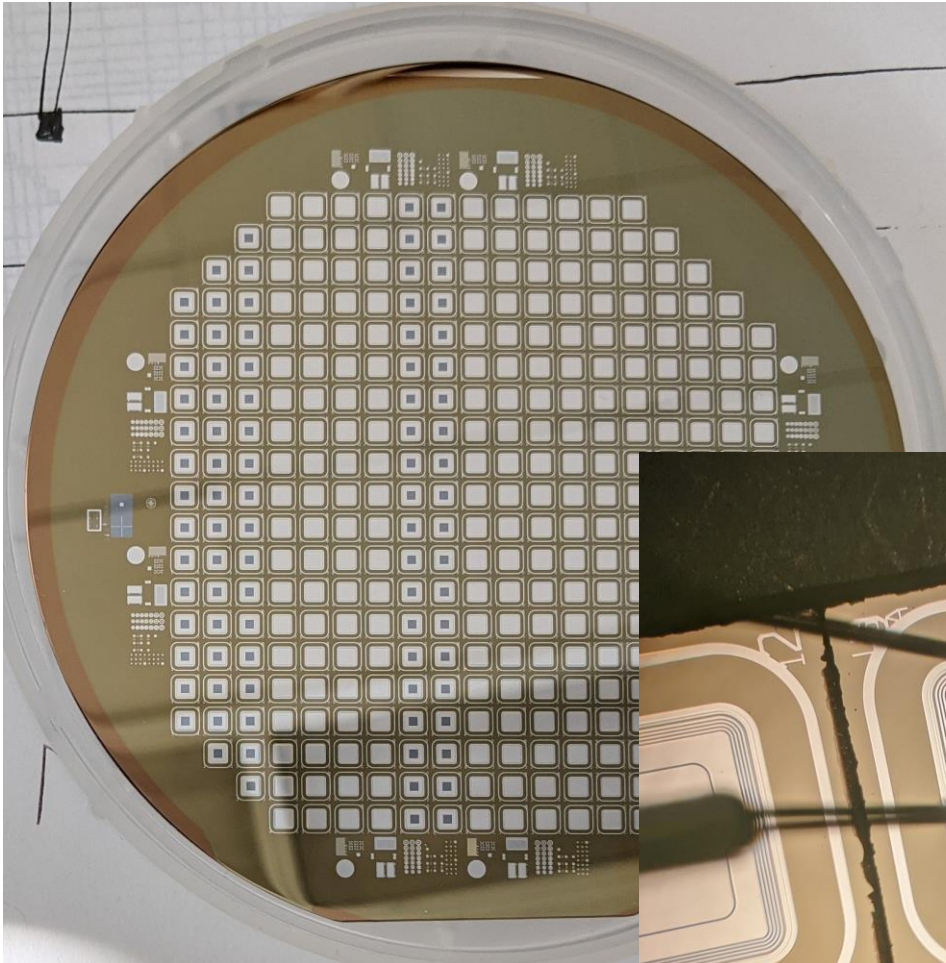


Laser dicing

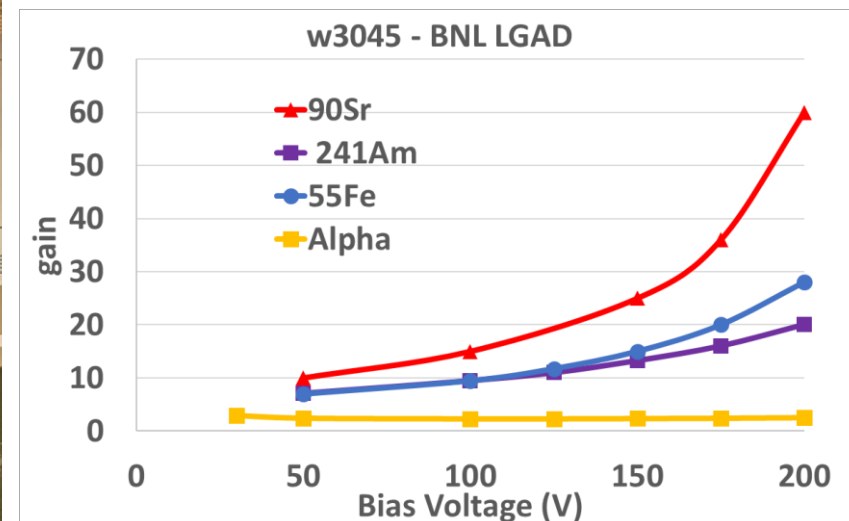
Design + TCAD + process flow: all in house

LGAD

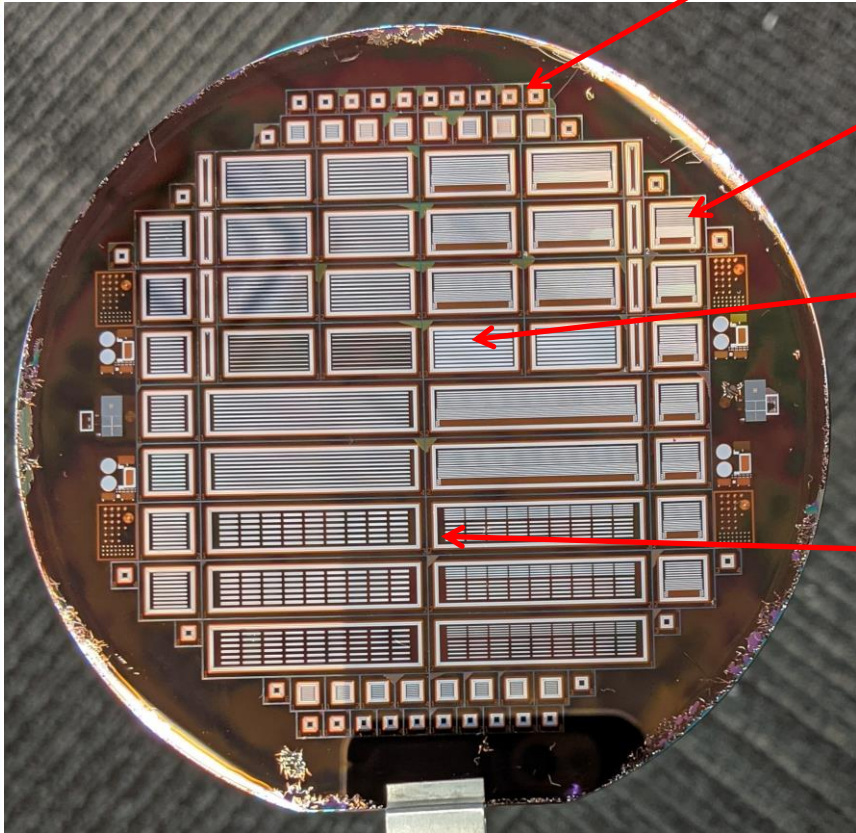
- Single channel LGADs
- 1.3 mm x1.3mm
- 20, 30, 50 um thick
- Fabricated for:
 - testing purposes (some solution brought to AC-LGADs)
 - Processed in parallel
 - Training of students and new hires
- Easier to test than AC-LGADs.



With present technology:
max gain = 60 for mipS



AC LGAD strip layout # 1



4 wafers fabricated
(2 50um + 2 20um)

Layout #1

		2x2 mm ²		
		pitch	gap	
7x		200	100	
		5x5 mm ²		
		pitch	gap	
7x		500	300	
7x		300,200,100	150,100,50	multipitch
		5x10mm ²		
		pitch	gap	
6x		500	300	
6x		300,200,100	150,100,50	multipitch
2x		500	400	
2x		500	200	
		5x25mm ²		
		pitch	gap	
2x		500	300	
2x		300,200,100	150,100,50	multipitch
2x		700	350	2.5mm long pixels
1x		700	450	2.5mm long pixels
1x		500,300	350,200	2.5mm long pixels, multipitch
2x		500,300	250,150	2.5mm long pixels, multipitch

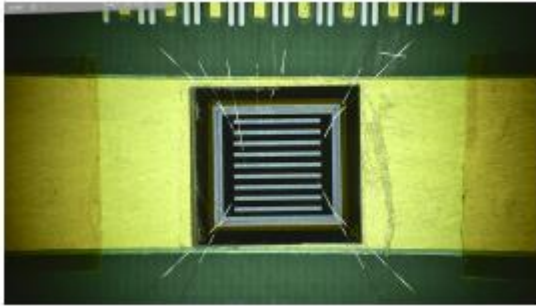
Pitch usually 500um
but smaller pitches used for test

Variations on the metal width

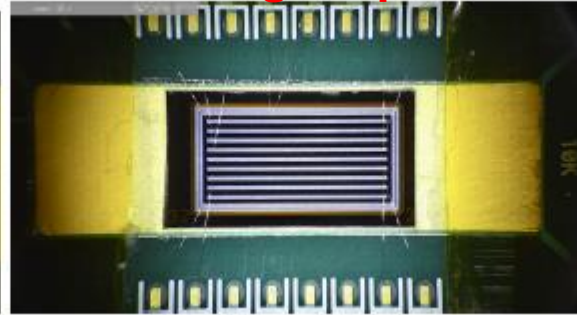
Variations on strip lengths

120GeV proton test beam @ FNAL

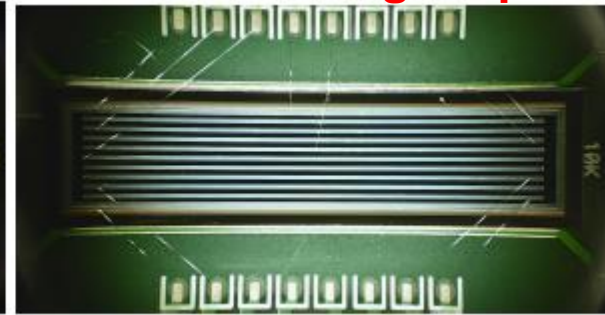
0.5cm long strips



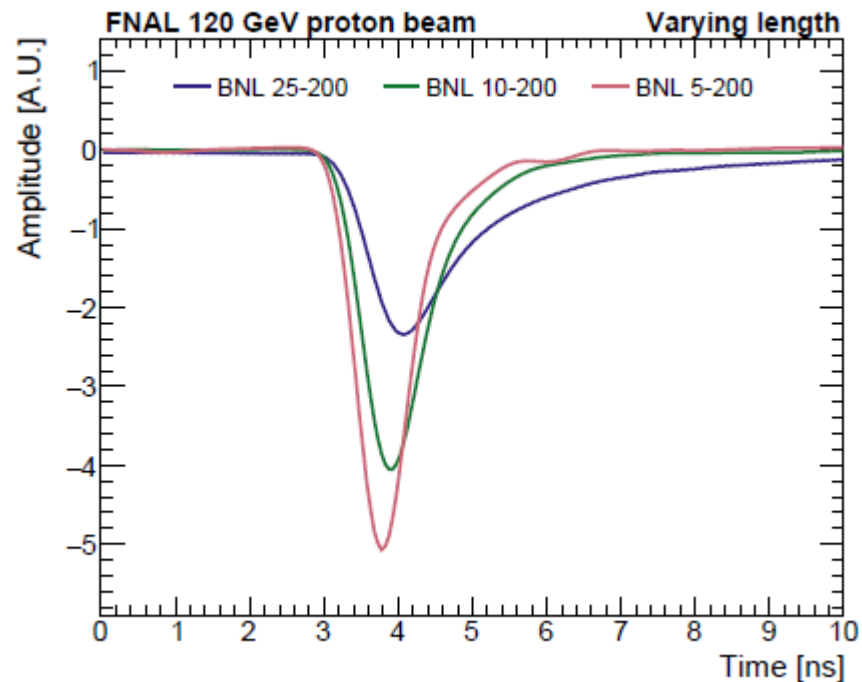
1cm long strips



2.5 cm long strips



~ 15 devices mounted on FNAL 16 ch RF boards and tested at FNAL

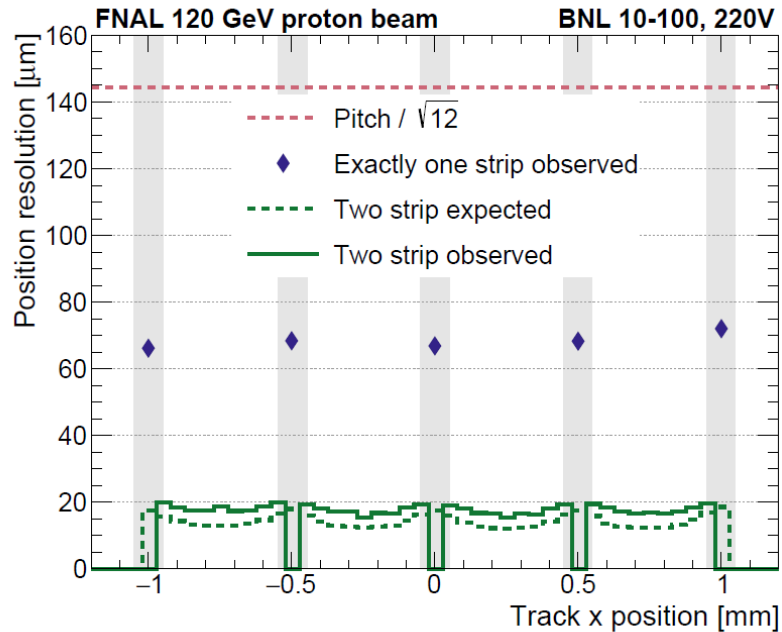


Average waveforms for different strip lengths (same strip width to help comparison).
Rise time significantly depends on strip length – possibly due to larger capacitance at the RF-amp inputs.

Not significant difference for different metal widths

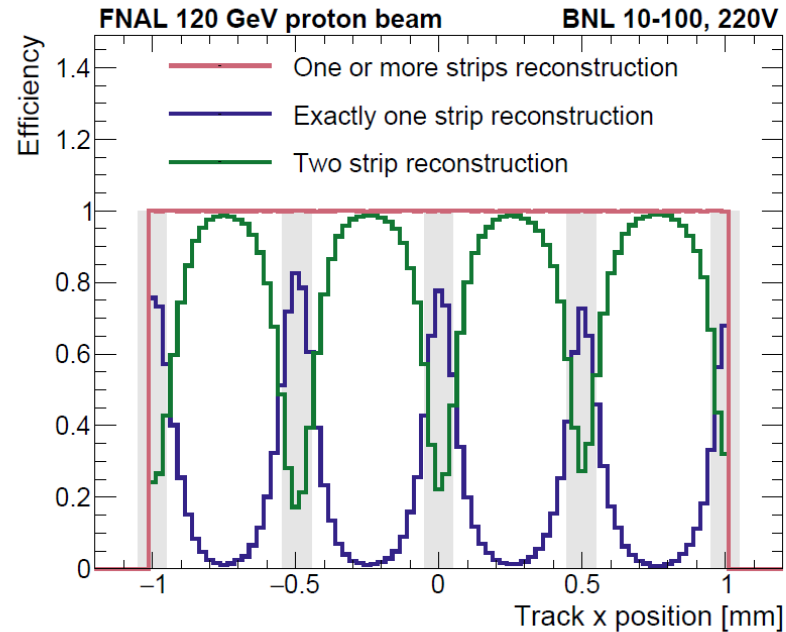
FNAL Test Beam Results - 1

Position resolution



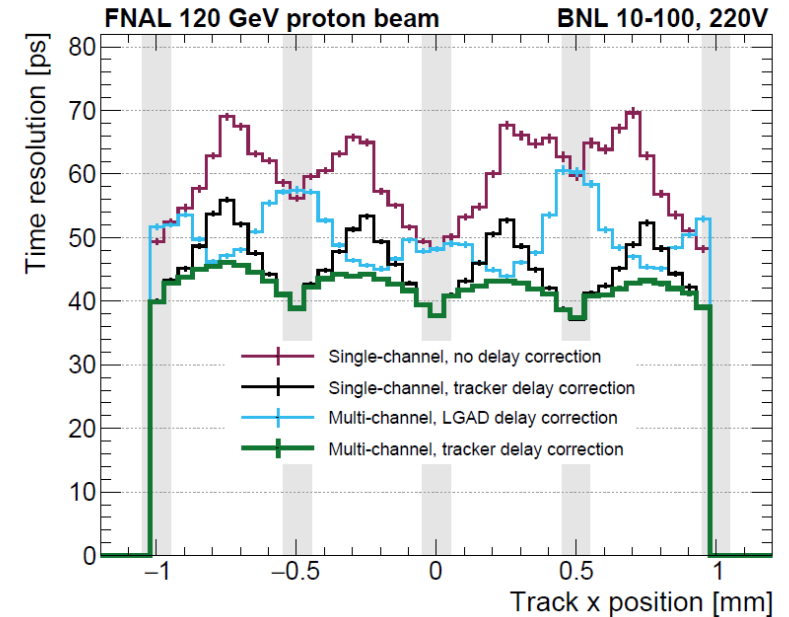
Interpolation from more strips brings the spatial resolution down to $> P/20$

Efficiency



100% fill factor: no dead area (except at the periphery)

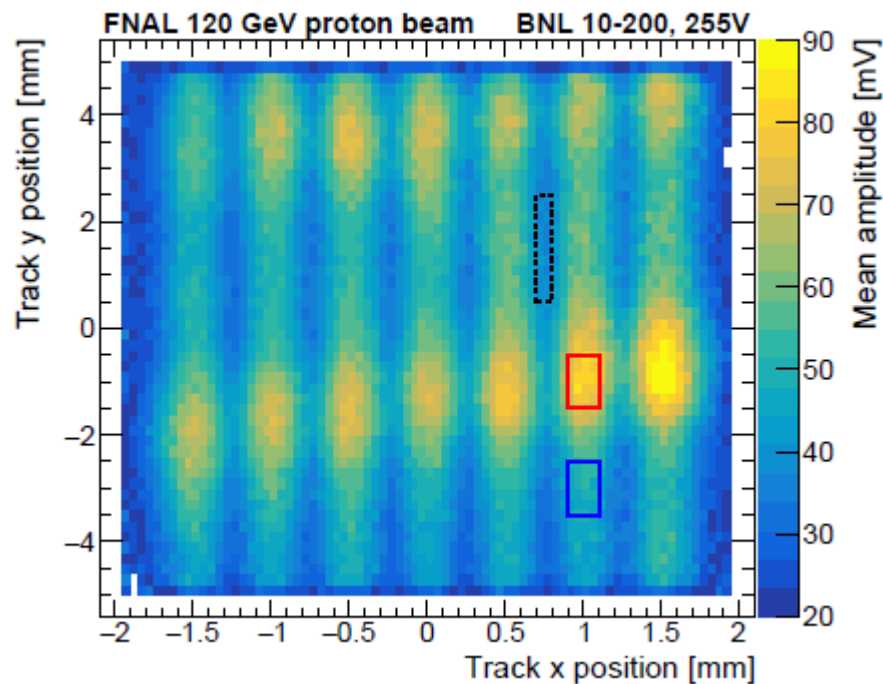
Timing



Time from 2+ channels, with correction for the propagation time to the RF input (via tracker)

FNAL Test Beam Results- 2

Issue of non uniformity: high- gain spots aligned on some tracks.
 Pointing to gain implant non-uniformity (1% difference makes a big difference)

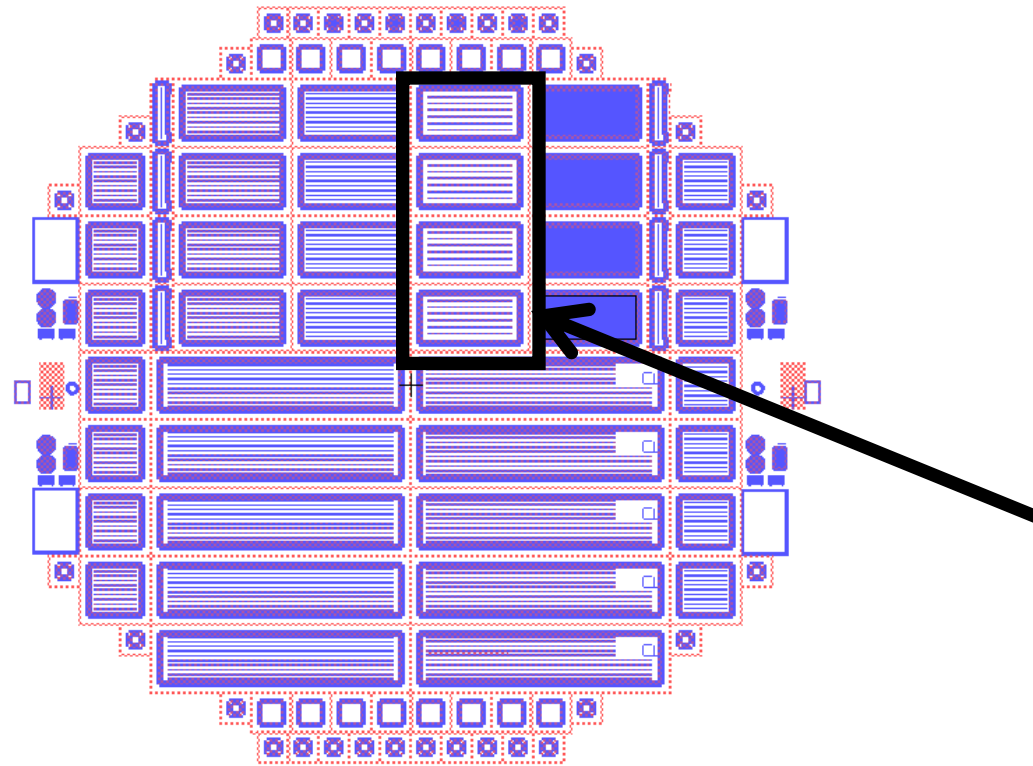


Considering hot spots only, timing and spatial resolution are better.
 These vales are to be expected in a uniform gain sensor.

Name Unit	Time resolution High gain ps	Spatial resolution			
		Exactly one strip		Two strip	
		Resolution μm	Eff. -	Resolution μm	Eff. -
BNL 5-200	30 ± 1	61 ± 1	35%	12 ± 1	65%
BNL 10-100	35 ± 1	69 ± 1	23%	19 ± 1	77%
BNL 10-200	32 ± 1	82 ± 1	43%	18 ± 1	57%
BNL 10-300	36 ± 1	83 ± 1	51%	16 ± 1	49%
BNL 25-200	51 ± 1	128 ± 1	82%	31 ± 1	18%

AC LGAD strip layout # 2

- Improve uniformity of gain
- Narrow strips for lower capacitance and to reduce single-strip events



multiplicity	mm x mm	Pitch (um)	Gap (um)
7	5x5	500	400
7	5x5	500	450
4	5x10	500	400
4	5x10	500	450
4	5x10	700	600
4	5x10	Zig Zag	
5	5x25	500	400/450
5	5x25	500	400 (l=2 or 2.5cm)

2+2 wafers fabricated
(2 50um + 2 20um)

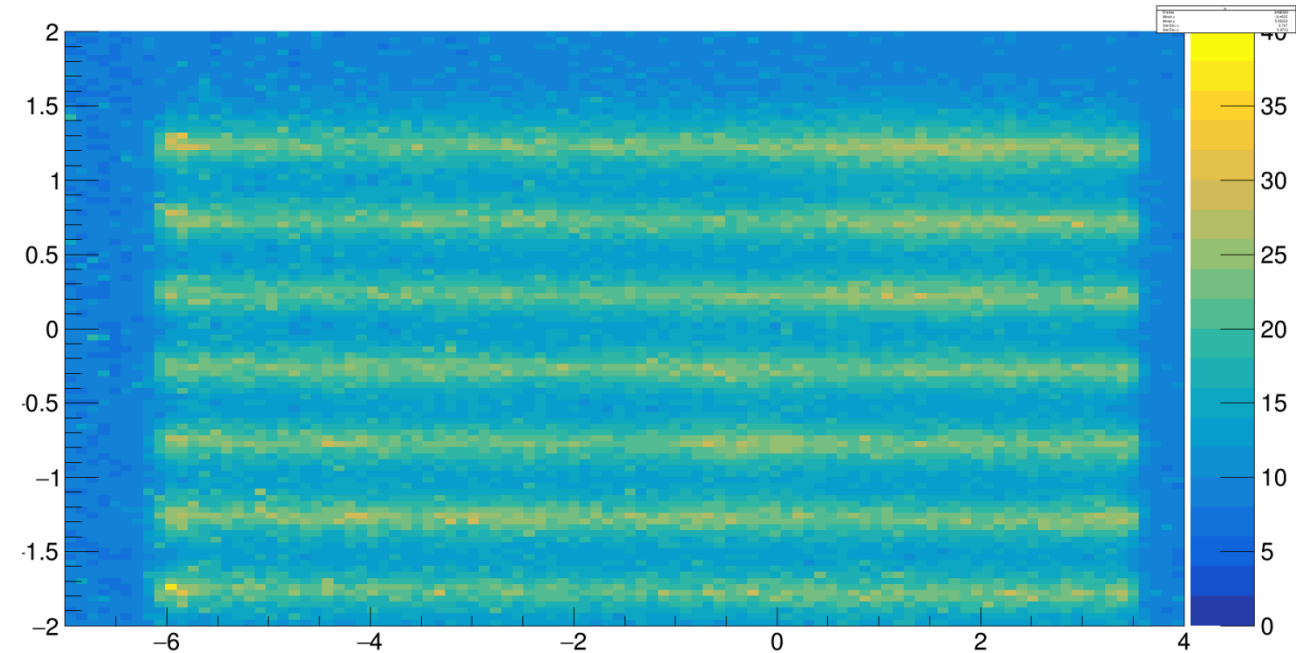
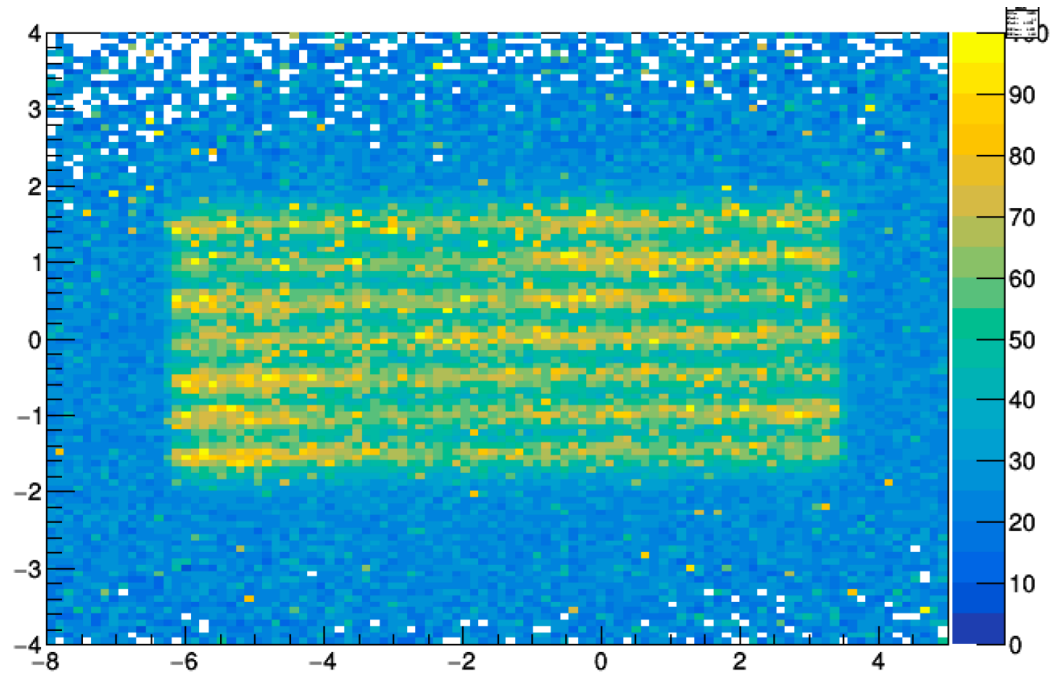
Test beam on-going @ FNAL

Some Very Preliminary Test Beam Results – January 2023

1-cm long strips, pitch = 500 μ m, strip width = 50 μ m

50 μ m thick epi layer

20 μ m thick epi layer



- Gain uniformity greatly improved
- Signal in 20 μ m thick epi layer within expectation
- Improvement of the gain would be beneficial

EICROC

Starting wafers: 50, 30, 20 um thick substrates

EICROC bump-bond compatible

All implants done,
Metal not ordered yet,
but designed.

**New ideas can be
implemented!!!**

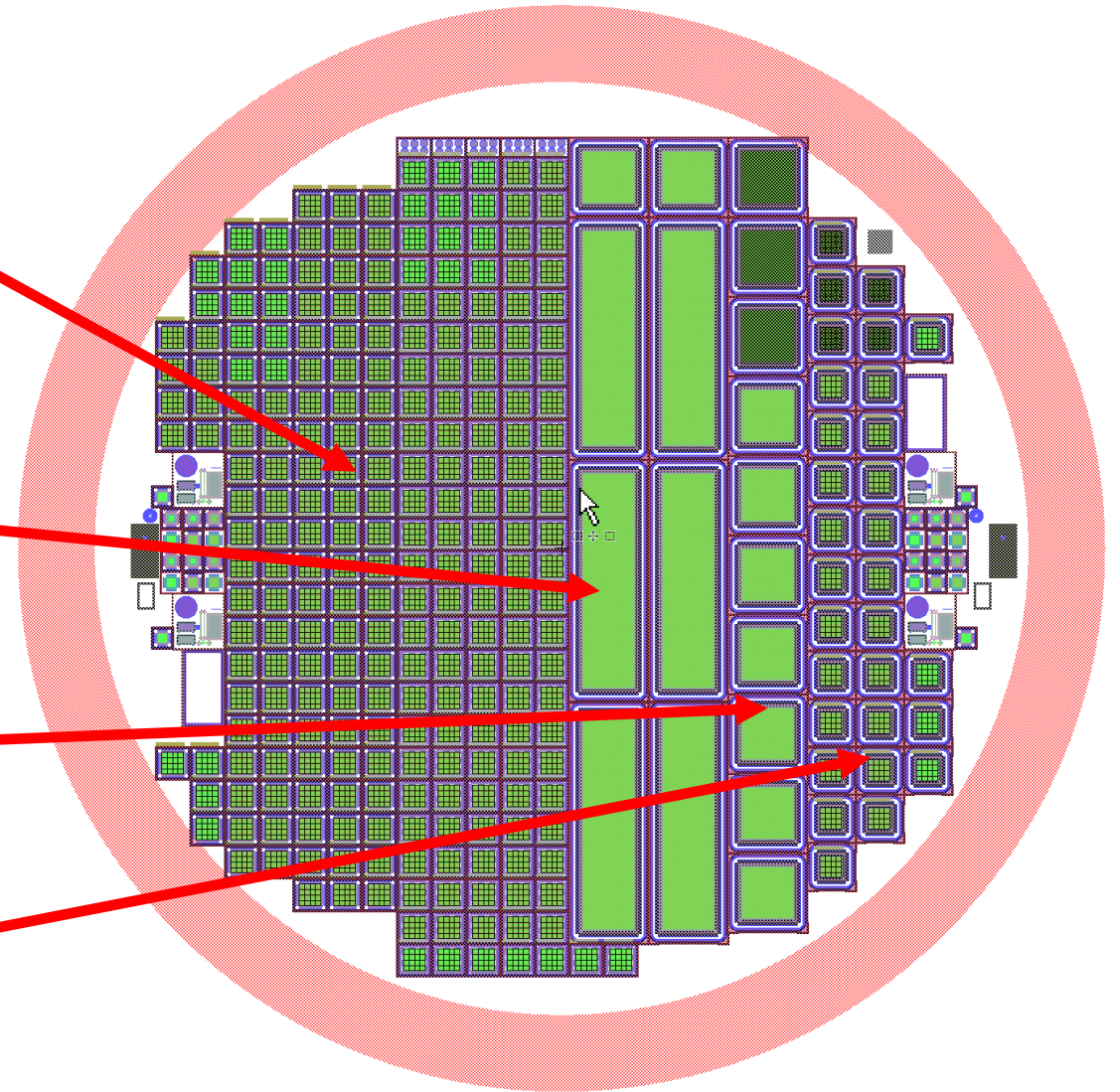
A fabrication at Hamamatsu
(HPK) is also on-going.
Variation of some process
parameters.

2cm x 0.5cm

0.5cm x 0.5cm

0.2cm x 0.2cm

Compatible with EICROC



Wafers out begin of February 2023.

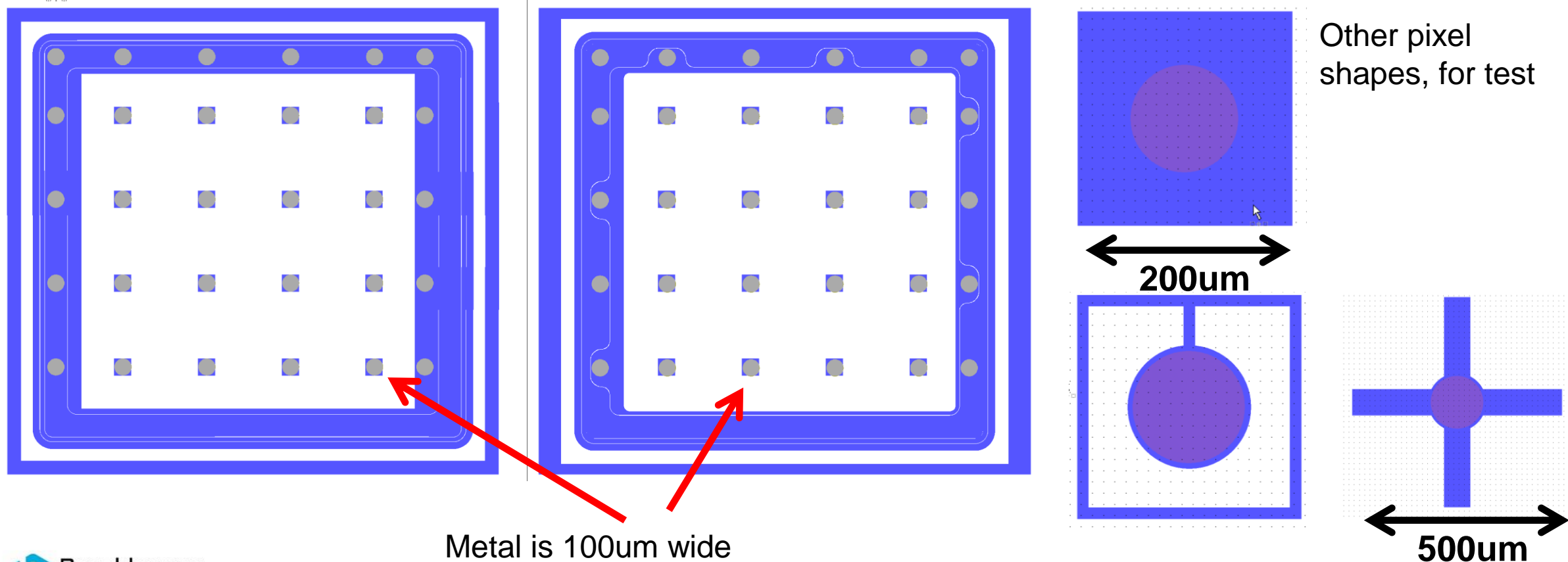
EICROC bump-bond compatible AC-LGAD

4x4 pixel, 500um pitch.

>10 pads for grounding (Guard Ring + *n*-resistive layer)

Different terminations.

Large number of devices allows a few variations of design (terminations and pixel shapes/dimensions)



Summary

BNL is engaged in the development of AC-LGADs:

- AC-LGAD strips
- EICROC compatible

AC-LGAD technology features 100% Fill Factor, $\sigma_x < P/20$ and $\sigma_t \sim 30\text{ps}$ (50um thick epi)

Some flaws corrected, but still room for improvements to be addressed in next batches:

- Larger gain
- Larger areas

HPK is also involved in prototyping for EPIC.

Active testing activity with test beams and in labs.